

ULTRA-THIN BODY TRANSISTOR WITH RECESSED SILICIDE CONTACTS

ABSTRACT OF THE DISCLOSURE

A semiconductor device (100), including a dielectric pedestal (220) located above and integral to a substrate (110) and having first sidewalls (230), a channel region (210) located above the dielectric pedestal (220) and having second sidewalls (240), and source and drain regions (410) opposing the channel region (210) and each substantially spanning one of the second sidewalls (240). An integrated circuit (800) incorporating the semiconductor device (100) is also disclosed, as well as a method of manufacturing the semiconductor device (100).